

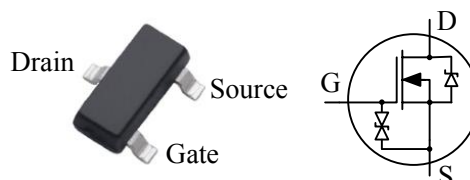
Depletion-Mode Power MOSFET

General Features

- ESD Improved Capability
- Depletion Mode (Normally On)
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- RoHS Compliant
- Halogen-free Available

BV_{DSX}	R_{DS(ON)} (Max.)	I_{DSS} (min)
150V	15 Ω	200mA

SOT-23



Applications

- New Energy Vehicles
- Industrial Automation
- Surge Protection
- Non-isolated Linear Power Supply
- Normally-on Switches
- Linear Amplifier
- Constant Current Source
- Telecom

Ordering Information

Part Number	Package	Marking	Remark
DMZ1520E	SOT-23	1520	Halogen Free

Absolute Maximum Ratings

T_A=25°C unless otherwise specified

Symbol	Parameter	DMZ1520E	Unit
V _{DSX}	Drain-to-Source Voltage ^[1]	150	V
V _{DGX}	Drain-to-Gate Voltage ^[1]	150	V
I _D	Continuous Drain Current	0.2	A
I _{DM}	Pulsed Drain Current ^[2]	0.6	
P _D	Power Dissipation	0.50	W
V _{GS}	Gate-to-Source Voltage	±20	V
V _{ESD}	Gate to Source ESD ^[3]	1500	V
	Source to Gate ESD ^[3]	1500	V
T _L	Soldering Temperature	300	°C
	Distance of 1.6mm from case for 10 seconds		
T _J and T _{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	DMZ1520E	Unit
R _{θJA}	Thermal Resistance, Junction-to-Ambient	250	K/W

Electrical Characteristics

OFF Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSX}	Drain-to-Source Breakdown Voltage	150	--	--	V	$V_{GS} = -10\text{V}$, $I_D = 250\mu\text{A}$
$I_{D(OFF)}$	Drain-to-Source Leakage Current	--	--	10	μA	$V_{DS} = 150\text{V}$, $V_{GS} = -10\text{V}$
		--	--	1.0	mA	$V_{DS} = 150\text{V}$, $V_{GS} = -10\text{V}$ $T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	± 20	μA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$

ON Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I_{DSS}	Saturated Drain-to-Source Current	200	--	--	mA	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	10	15	Ω	$V_{GS} = 0\text{V}$, $I_D = 100\text{mA}$ ^[4]
$V_{GS(OFF)}$	Gate-to-Source Cut-off Voltage	-3.5	--	-5.5	V	$V_{DS} = 3\text{V}$, $I_D = 8\mu\text{A}$
gfs	Forward Transconductance	--	0.24	--	S	$V_{DS} = 10\text{V}$, $I_D = 100\text{mA}$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{ISS}	Input Capacitance	--	12.8	--	pF	$V_{GS} = -10\text{V}$ $V_{DS} = 25\text{V}$ $f = 1.0\text{MHz}$
C_{OSS}	Output Capacitance	--	5.4	--		
C_{RSS}	Reverse Transfer Capacitance	--	3.3	--		
Q_G	Total Gate Charge	--	3	--	nC	$V_{GS} = -10\text{V} \sim 0\text{V}$ $V_{DS} = 75\text{V}$, $I_D = 200\text{mA}$
Q_{GS}	Gate-to-Source Charge	--	0.23	--		
Q_{GD}	Gate-to-Drain (Miller) Charge	--	1.1	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(on)}$	Turn-on Delay Time	--	7	--	ns	$V_{GS} = -10\text{V} \sim 0\text{V}$ $V_{DD} = 75\text{V}$, $I_D = 200\text{mA}$ $R_G = 20\Omega$
t_{rise}	Rise Time	--	16	--		
$t_{d(off)}$	Turn-off Delay Time	--	25	--		
t_{fall}	Fall Time	--	120	--		

Source-Drain Diode Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V_{SD}	Diode Forward Voltage	--	--	1.2	V	$I_{SD} = 200\text{mA}$, $V_{GS} = -10\text{V}$

NOTE:

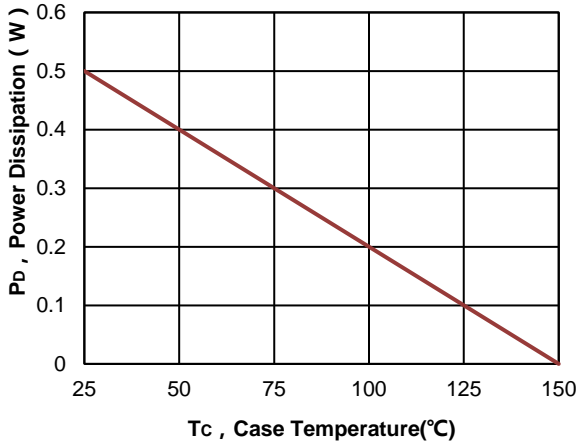
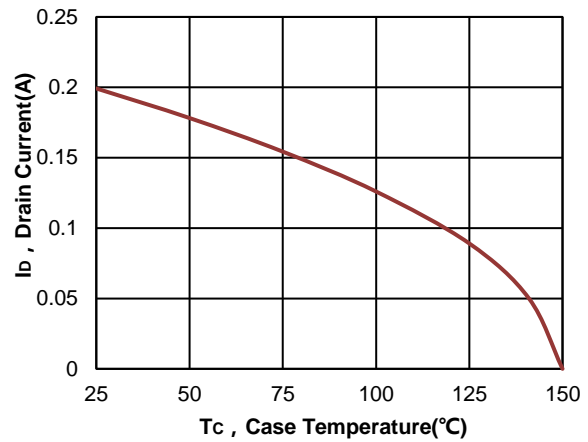
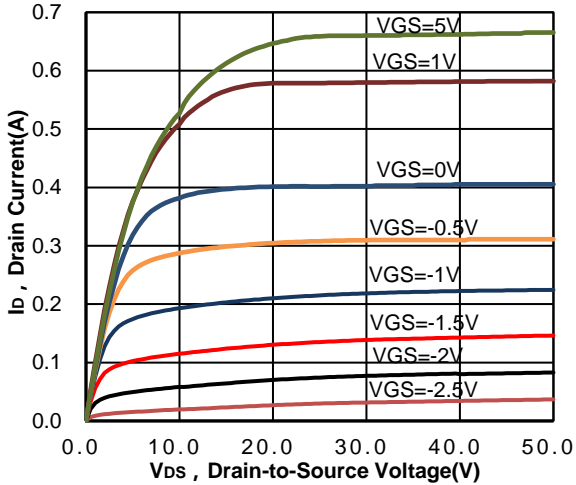
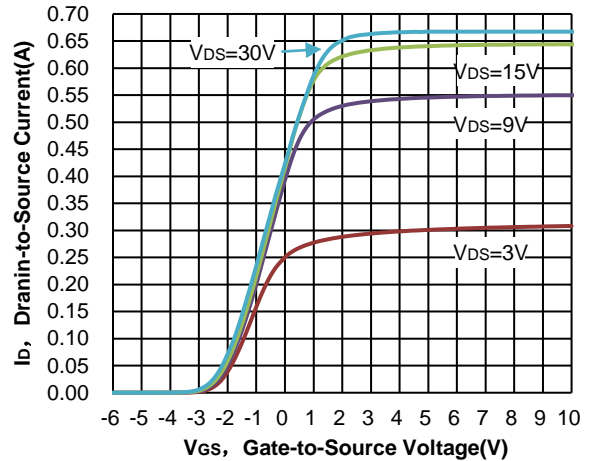
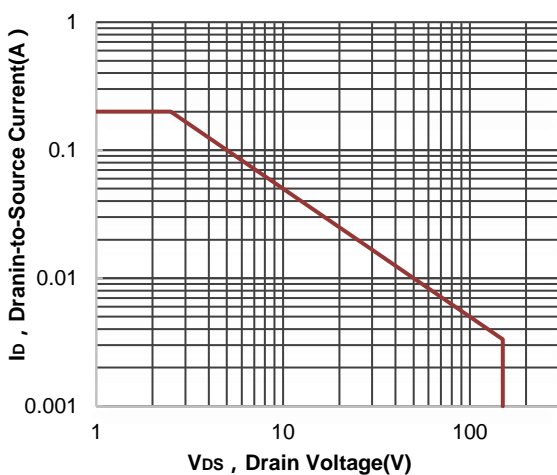
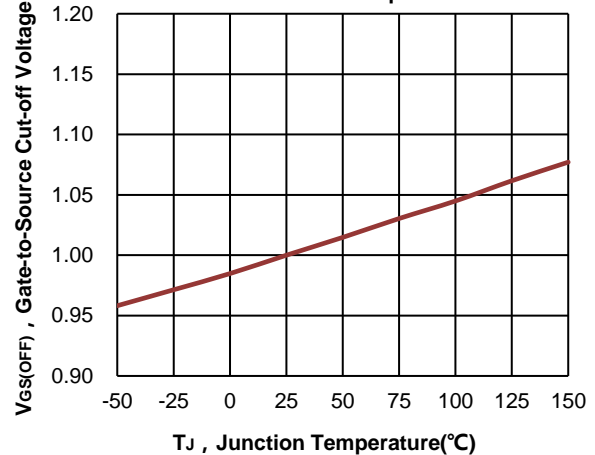
[1] $T_J = +25^\circ\text{C}$ to $+150^\circ\text{C}$

[2] Repetitive rating, pulse width limited by maximum junction temperature.

[3] The test is based on JEDEC EIA/JESD22-A114(HBM).

[4] Pulse width $\leq 380\mu\text{s}$; duty cycle $\leq 2\%$.

Typical Characteristics

Figure 1. Maximum Power Dissipation vs. Case Temperature

Figure 2. Maximum Continuous Drain Current vs. Case Temperature

Figure 3. Typical Output Characteristics

Figure 4. Typical Transfer Characteristics

Figure 5. Maximum Rated Safe Operating Area

Figure 6. Typical Gate-to-Source Cut-off Voltage vs. Junction Temperature


Typical Application

In the application circuits of industrial automation, automotive electronics, and new energy, DMZ1520E can be used to power LDO. As shown in Figure 7, only one DMZ1520E is used in the circuit, which can convert the high input voltage into a stable low voltage to supply power to the LDO, and at the same time provide transient surge suppression for the LDO. The input voltage and output voltage of the LDO satisfy the relationship: $V_S = V_{out} + |V_{GS(OFF)}|$. The circuit has a fast response speed, a simple structure, and can effectively save costs.

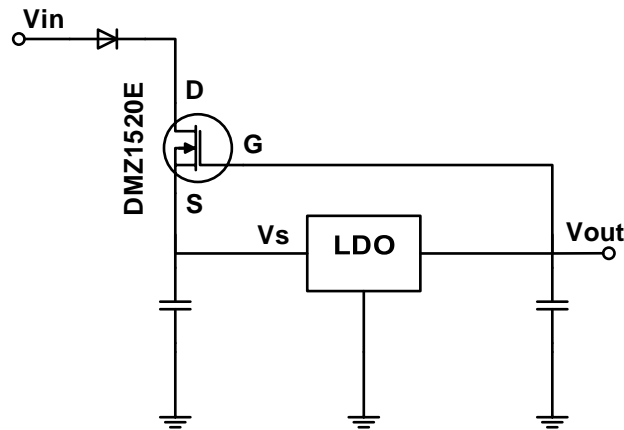


Figure 7. The Circuit of DMZ1520E to power supply for LDO

Using the sub-threshold characteristics of the DMZ1520E, it can form a stable current source with the resistor R. Its basic application is shown in Figure 8:

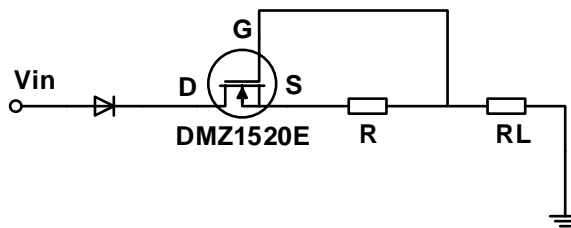
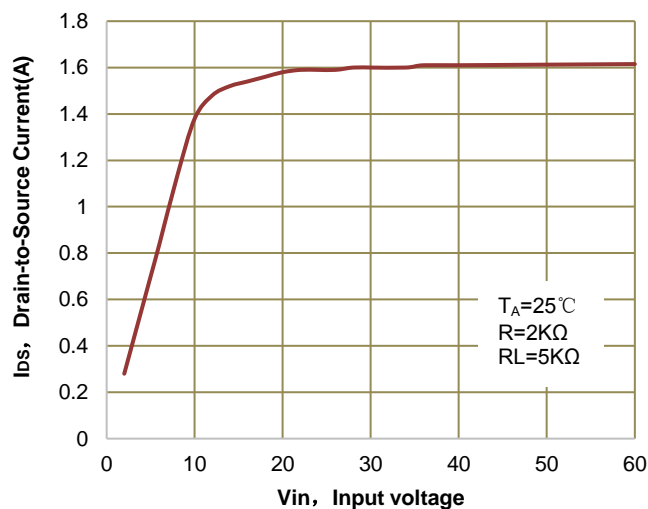


Figure 8. The Circuit of DMZ1520E and resistor form constant current source

Using the sample with $V_{GS(OFF)} = -4.3V$ ($@V_{DS} = 3V, I_{DS} = 8\mu A$) to test according to the circuit shown in Figure 8, the result is shown in Figure 9:

Figure 9. Typical Drain-to-Source Current vs. Input voltage



In the Type-C/PD charger circuit, DMZ1520E and resistor R form a constant current source, which supplies stable power to InnoSwitch. The structure of the circuit is simple, and the DMZ1520E can also provide transient surge suppression for InnoSwitch. The circuit is shown in Figure 10:

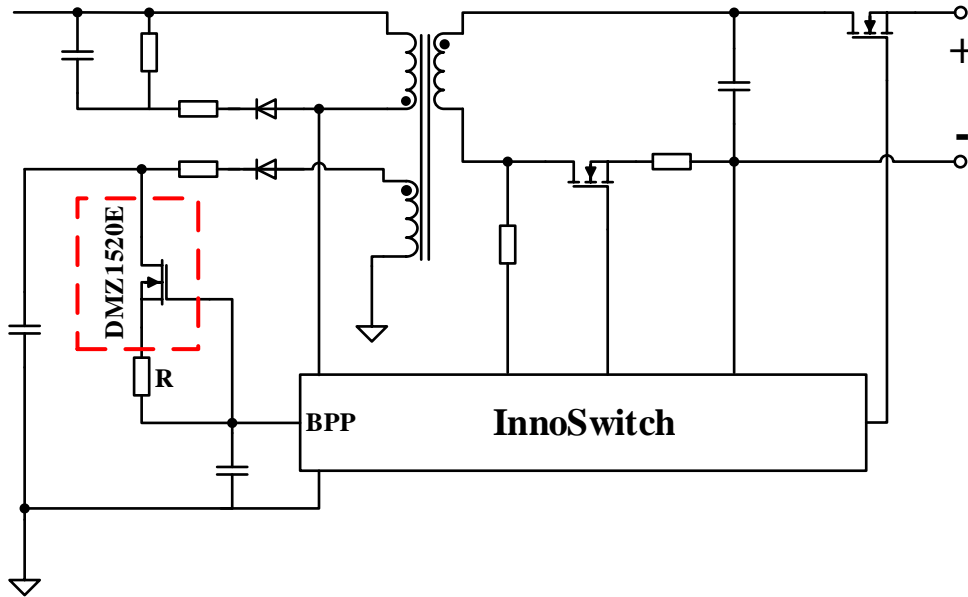
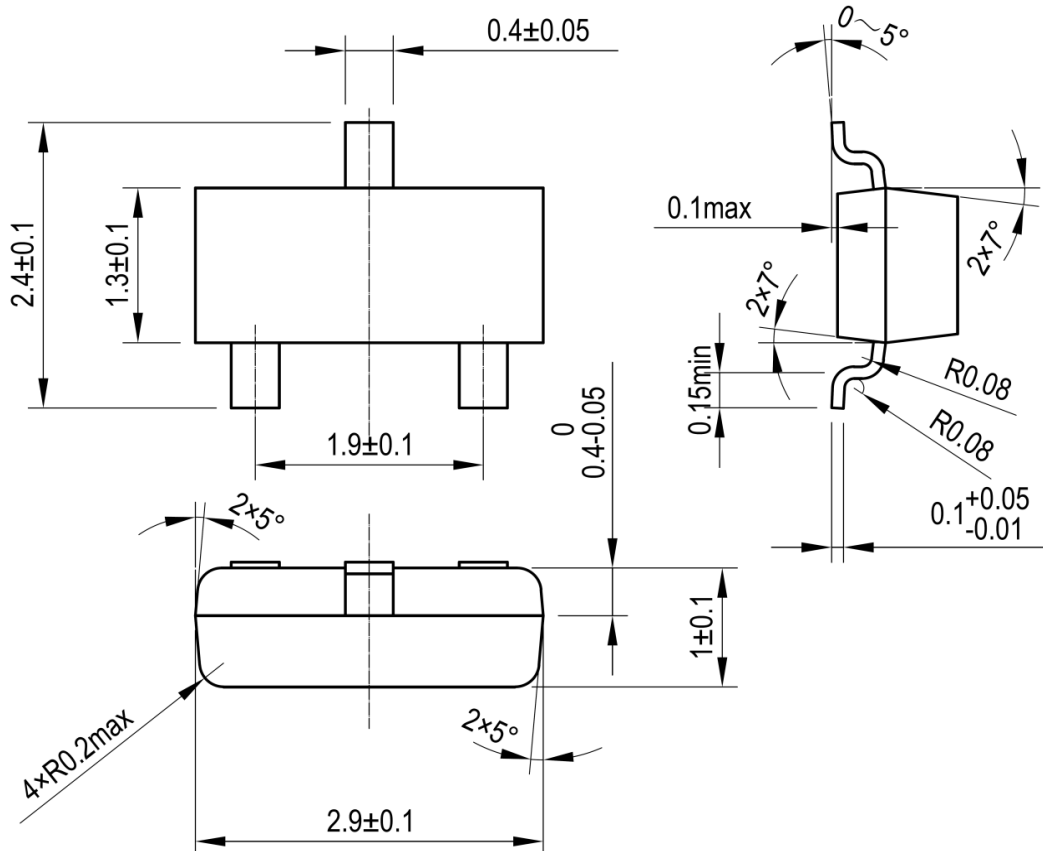


Figure 10. Constant current source circuit with DMZ1520E

Package Dimensions

SOT-23



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